High-voltage Amplifier Transistor (-120V, -50mA)

Datasheet

Parameter	Value
V _{CEO}	-120V
I _C	-50mA

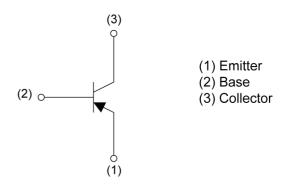
Outline



Features

- 1)High breakdown voltage. (BV_{CEO}=-120V)
- 2)Complements the 2SC4102/2SC3906K.

•Inner circuit



Application

HIGH VOLTAGE AMPLIFIER

Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	hFE rank	Marking
2SA1579	UMT3	2021	T106	180	8	3000	RS	R
2SA1514K	SMT3	2928	T146	180	8	3000	RS	R

• Absolute maximum ratings ($T_a = 25$ °C)

Parameter			Values	Unit
Collector-base voltage			-120	V
Collector-emitter voltage			-120	V
Emitter-base voltage			-5	V
Collector current			-50	mA
Davier disable ties	2SA1579	D *1	200	\^/
Power dissipation	2SA1514K	P_{D}^{*1}	200	mW
Junction temperature			150	°C
Range of storage temperature			-55 to +150	°C

● Electrical characteristics (T_a = 25°C)

Davamatav	Cymabal	Canditions	Values			Lloit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV _{CBO}	I _C = -50μA	-120	-	-	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = -1mA	-120	1	1	V
Emitter-base breakdown voltage	BV _{EBO}	I _E = -50μA	-5	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} = -100V	-	-	-500	nA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V	-	1	-500	nA
Collector-emitter saturation voltage	V _{CE(sat)} *2	$I_C = -10 \text{mA}, I_B = -1 \text{mA}$	-	-	-500	mV
DC current gain	h _{FE}	$V_{CE} = -6V, I_{C} = -2mA$	180	1	560	•
Transition frequency	f _T	$V_{CE} = -12V, I_{E} = 2mA,$ f = 100MHz	-	140	-	MHz
Output capacitance	C _{ob}	$V_{CB} = -12V, I_{E} = 0A,$ f = 1MHz	-	3.2	-	pF

hFE values are calssified as follows:

rank	R	S	-	-	-
h _{FE}	180-390	270-560	-	-	-

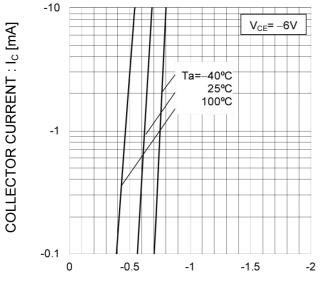
2/7

^{*1} Each terminal mounted on a reference land.

^{*2} Pulsed

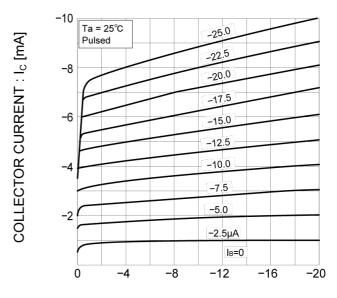
● Electrical characteristic curves(T_a = 25°C)

Fig.1 Ground Emitter Propagation Characteristics



BASE TO EMITTER VOLTAGE : $V_{\text{BE}}\left[V\right]$

Fig.2 Typical Output Characteristics



COLLECTOR TO EMITTER VOLTAGE: VCE [V]

Fig.3 DC Current Gain vs. Collector Current (I)

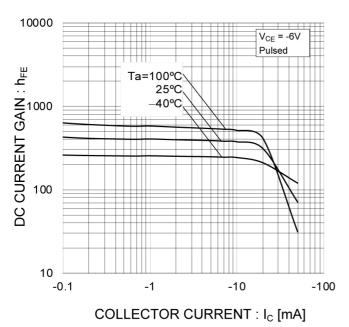
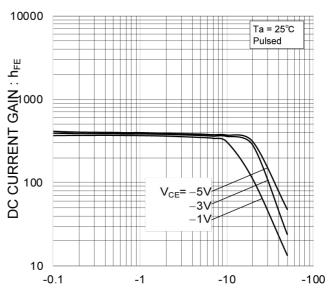


Fig.4 DC Current Gain vs. Collector Current (II)



COLLECTOR CURRENT : I_C [mA]

● Electrical characteristic curves(T_a = 25°C)

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

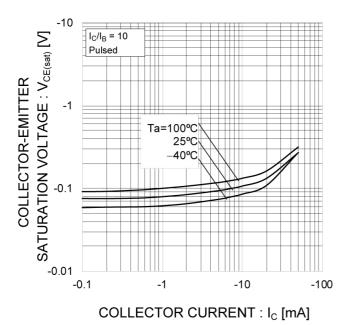


Fig.6 Collector-Emitter Saturation
Voltage vs. Collector Current (II)

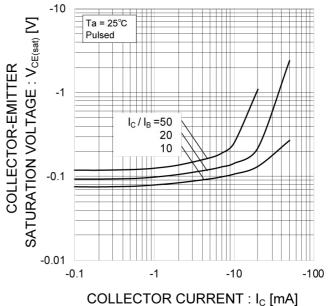


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

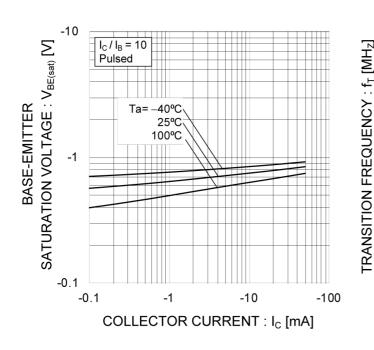
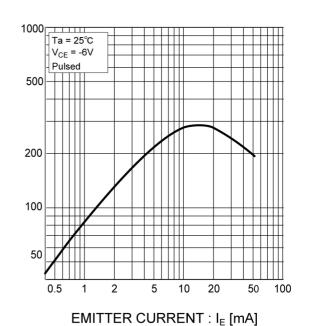


Fig.8 Gain Bandwidth Product vs. Emitter Current



● Electrical characteristic curves(T_a = 25°C)

Fig.9 Collector Output Capacitance vs. Collector-Base Voltage

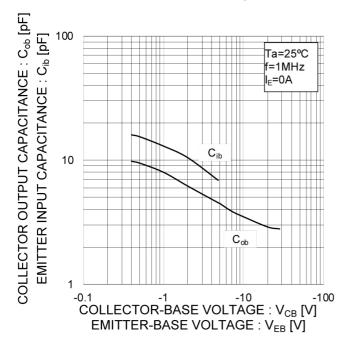


Fig.10 Safe Operating Area

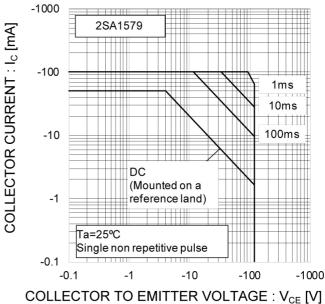
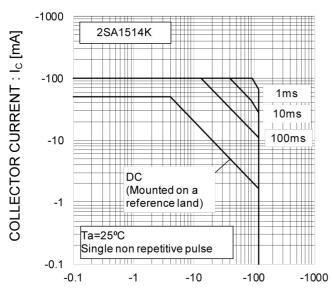


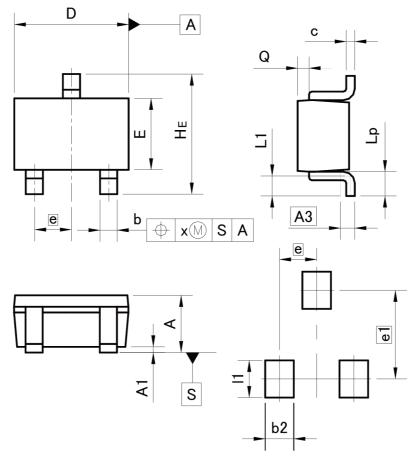
Fig.11 Safe Operating Area



COLLECTOR TO EMITTER VOLTAGE: VCE [V]

Dimensions

UMT3



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	0.80	1.00	0.031	0.039	
A1	0.00	0.10	0.000	0.004	
A3	0.5	25	0.0	10	
b	0.15	0.30	0.006	0.012	
С	0.10	0.20	0.004	0.008	
D	1.90	2.10	0.075	0.083	
E	1.15	1.35	0.045	0.053	
е	0.0	65	0.026		
HE	2.00	2.20	0.079	0.087	
L1	0.20	0.50	0.008	0.020	
Lp	0.25	0.55	0.010	0.022	
Q	0.10	0.30	0.004	0.012	
х	_	0.10	_	0.004	

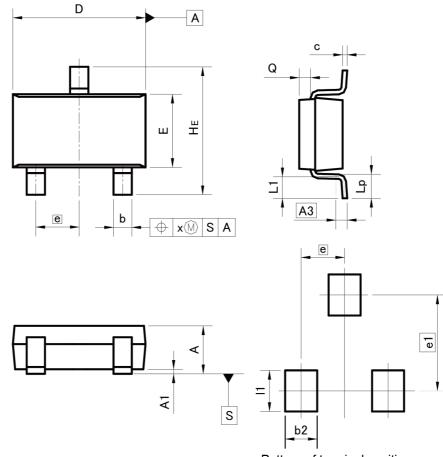
DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
b2	-	0.50	1	0.020	
e1	1.55		0.0	61	
11	-	0.65	ı	0.026	

Dimension in mm/inches



Dimensions

SMT3



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.00	1.30	0.039	0.051	
A1	0.00	0.10	0.000	0.004	
A3	0.:	25	0.0	10	
b	0.35	0.50	0.014	0.020	
С	0.09	0.25	0.004	0.010	
D	2.80	3.00	0.110	0.118	
E	1.50	1.80	0.059	0.071	
е	0.9	95	0.037		
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.20	0.30	0.008	0.012	
х	_	0.10	_	0.004	
У	_	0.10	_	0.004	

DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
b2	_	0.60	-	0.024	
e1	2.10		0.0	83	
11	_	0.90	_	0.035	

Dimension in mm/inches



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